SLOS289D - DECEMBER 1999 - REVISED FEBRUARY 2002

**Operational Amplifier** 

TLV4112

D, DGN, OR P PACKAGE

(TOP VIEW)

 $\square$   $\vee_{DD}$ 

□ 20UT

□ 2IN+

2IN-

10UT□

1IN-□

1IN+□☐ GND□☐

- High Output Drive . . . >300 mA
- Rail-To-Rail Output
- Unity-Gain Bandwidth . . . 2.7 MHz
- Slew Rate . . . 1.5 V/μs
- Supply Current . . . 700 μA/Per Channel
- Supply Voltage Range . . . 2.5 V to 6 V
- Specified Temperature Range:
  - $T_A = 0$ °C to 70°C . . . Commercial Grade
  - T<sub>A</sub> =  $-40^{\circ}$ C to  $125^{\circ}$ C . . . Industrial Grade
- Universal OpAmp EVM

#### description

The TLV411x single supply operational amplifiers provide output currents in excess of 300 mA at 5 V. This enables standard pin-out amplifiers to be used as high current buffers or in coil driver applications. The TLV4110 and TLV4113 come with a shutdown feature.

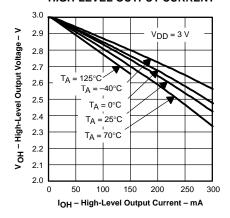
The TLV411x is available in the ultra small MSOP PowerPAD™ package, which offers the exceptional thermal impedance required for amplifiers delivering high current levels.

All TLV411x devices are offered in PDIP, SOIC (single and dual) and MSOP PowerPAD (dual).

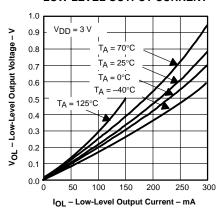
#### **FAMILY PACKAGE TABLE**

DEVICE	NUMBER OF	PAC	KAGE TY	PES	SHUTDOWN	UNIVERSAL
DEVICE	CHANNELS	MSOP	PDIP	SOIC	SHOTDOWN	EVM BOARD
TLV4110	1	8	8	8	Yes	
TLV4111	1	8	8	8	_	Refer to the EVM Selection Guide
TLV4112	2	8	8	8	_	(Lit# SLOU060)
TLV4113	2	10	14	14	Yes	

# HIGH-LEVEL OUTPUT VOLTAGE vs HIGH-LEVEL OUTPUT CURRENT



# LOW-LEVEL OUTPUT VOLTAGE vs LOW-LEVEL OUTPUT CURRENT





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PowerPAD is a trademark of Texas Instruments.

TEXAS INSTRUMENTS

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#### **TLV4110 AND TLV4111 AVAILABLE OPTIONS**

		PACKAGED DEVI	CES	
TA	SMALL OUTLINE	MSOP	PLASTIC DIP	
'A	(D)†‡	SMALL OUTLINE (DGN) <sup>†</sup>	SYMBOL	(P)
0°C to 70°C	TLV4110CD	TLV4110CDGN	xxTIAHL	TLV4110CP
0 0 10 70 0	TLV4111CD	TLV4111CDGN	xxTIAHN	TLV4111CP
-40°C to 125°C	TLV4110ID	TLV4110IDGN	xxTIAHM	TLV4110IP
-40 C to 125 C	TLV4111ID	TLV4111IDGN	xxTIAHO	TLV4111IP

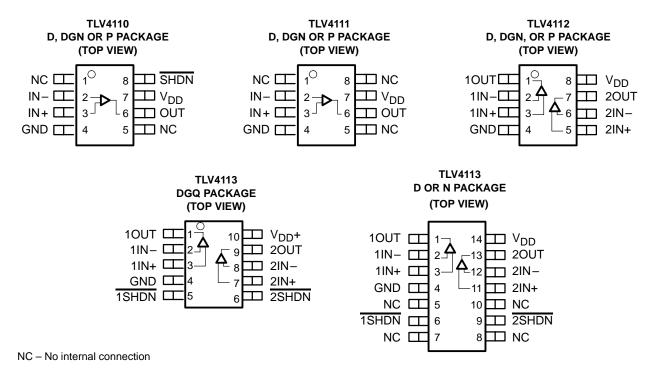
<sup>†</sup> This package is available taped and reeled. To order this packaging option, add an R suffix to the part number (e.g., TLV4110CDR).

#### **TLV4112 AND TLV4113 AVAILABLE OPTIONS**

		PACKAGED DEVICES								
TA	SMALL OUTLINE (D)†‡			PLASTIC DIP						
'A		SMALL OUTLINE (DGN)†	SYMBOL	SMALL OUTLINE (DGQ)†	SYMBOL	(P)				
0°C to 70°C	TLV4112CD	TLV4112DGN	xxTIAHP	_	_	TLV4112CP				
0 0 10 70 0	TLV4113CD	_	_	TLV4113CDGQ	xxTIAHR	TLV4113CN				
-40°C to 125°C	TLV4112ID	TLV4112IDGN	xxTIAHQ	_	_	TLV4112IP				
-40 C to 125 C	TLV4113ID	_	_	TLV4113IDGQ	xxTIAHS	TLV4113IN				

<sup>†</sup> This package is available taped and reeled. To order this packaging option, add an R suffix to the part number (e.g., TLV4112CDR).

#### **TLV411x PACKAGE PINOUTS**





<sup>‡</sup> In the SOIC package, the maximum RMS output power is thermally limited to 350 mW; 700 mW peaks can be driven, as long as the RMS value is less than 350 mW.

<sup>‡</sup> In the SOIC package, the maximum RMS output power is thermally limited to 350 mW; 700 mW peaks can be driven, as long as the RMS value is less than 350 mW.

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### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V <sub>DD</sub> (see Note 1)	7 V
Differential input voltage, V <sub>ID</sub>	±V <sub>DD</sub>
Input voltage range, V <sub>I</sub>	
Output current, IO (see Note 2)	
Continuous /RMS output current, I <sub>O</sub> (each output of amplifier): T <sub>J</sub> ≤ 105°C	
T <sub>.J</sub> ≤ 150°C	110 mA
Peak output current, I <sub>O</sub> (each output of amplifier: T <sub>.1</sub> ≤ 105°C	500 mA
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T <sub>A</sub> : C suffix	0°C to 70°C
I suffix	
Maximum junction temperature, T <sub>.j.</sub>	150°C
Storage temperature range, T <sub>stq</sub>	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values, except differential voltages, are with respect to GND.

2. To prevent permanent damage the die temperature must not exceed the maximum junction temperature.

#### **DISSIPATION RATING TABLE**

PACKAGE	(°C/W) θJC	θJA (°C/W)	T <sub>A</sub> ≤ 25°C POWER RATING	T <sub>A</sub> = 125°C POWER RATING
D (8)	38.3	176	710 mW	142 mW
D (14)	26.9	122.3	1022 mW	204.4 mW
DGN (8) <sup>‡</sup>	4.7	52.7	2.37 W	474.4 mW
DGQ (10) <sup>‡</sup>	4.7	52.3	2.39 W	478 mW
P (8)	41	104	1200 mW	240.4 mW
N (14)	32	78	1600 mW	320.5 mW

<sup>\$\</sup>frac{1}{2}\$ See The Texas Instruments document, PowerPAD Thermally Enhanced Package Application Report (literature number SLMA002), for more information on the PowerPAD package. The thermal data was measured on a PCB layout based on the information in the section entitled Texas Instruments Recommended Board for PowerPAD on page 33 of the before mentioned document.

### recommended operating conditions

			MIN	MAX	UNIT
Supply voltage, V <sub>DD</sub>			2.5	6	V
Common-mode input voltage range, V <sub>ICR</sub>			0	V <sub>DD</sub> -1.5	V
Operating free-air temperature, T <sub>A</sub>	C-suffix	C-suffix		70	°C
	I-suffix	I-suffix		125	C
	\/(op)	$V_{DD} = 3 V$	2.1		V
	V(on)	$V_{DD} = 5 V$	3.8		
Shutdown turnon/off voltage level§	V(off)	$V_{DD} = 3 V$		0.9	V
	V(OII)	$V_{DD} = 5 V$		1.65	

<sup>§</sup> Relative to GND



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# electrical characteristics at recommend operating conditions, $V_{DD}$ = 3 V and 5 V (unless otherwise noted)

#### dc performance

	PARAMETER	TEST CON	DITIONS	T <sub>A</sub> †	MIN	TYP	MAX	UNITS
1/10	Input offeet veltoge	., ., .,		25°C		175	3500	\/
VIO	Input offset voltage	$V_{IC} = V_{DD}/2$ , $R_L = 100 \Omega$ ,	$V_O = V_{DD}/2$ , Ro = 50.0	Full range			4000	μV
αVIO	Offset voltage draft	110 32,	115 - 00 22	25°C		3		μV/°C
CMBB	Common-mode rejection ratio	$V_{DD} = 3 \text{ V},$ $R_S = 50 \Omega$	$V_{IC} = 0$ to 2 V,	25°C		63		dB
CMRR		$V_{DD} = 5 \text{ V},$ $R_S = 50 \Omega$	$V_{IC} = 0 \text{ to } 4 \text{ V},$	25°C		68		αв
		V <sub>DD</sub> = 3 V,	R <sub>L</sub> =100 Ω	25°C	78	84		
				Full range	67			
		V <sub>O(PP)</sub> =0 to 1V	D. 10 kg	25°C	85	100		
<b> </b>	Large-signal differential voltage		R <sub>L</sub> =10 kΩ	Full range	75			dB
AVD	amplification		D: 400.0	25°C	88	94		иь
		V <sub>DD</sub> = 5 V,	R <sub>L</sub> =100 Ω	Full range	75			
		V <sub>O(PP)</sub> =0 to 3V	D 401-0	25°C	90	110		
			R <sub>L</sub> =10 kΩ	Full range	85			

<sup>†</sup> Full range is 0°C to 70°C for C suffix and –40°C to 125°C for I suffix. If not specified, full range is –40°C to 125°C.

#### input characteristics

PARAMETER		TEST CO	TEST CONDITIONS		MIN	TYP	MAX	UNITS	
				25°C		0.3	25	- - pA	
IIO	Input offset current	$V_{IC} = V_{DD}/2$	TLV411xC	Full range			50		
			TLV411xI	Tull larige			250		
			-	25°C		0.3	50		
I <sub>IB</sub>	Input bias current	$V_O = V_{DD}/2$ , $R_S = 50 \Omega$	TLV411xC	Full rooms			100		
		115 = 30 22	TLV411xI	Full range			500		
r <sub>i(d)</sub>	Differential input resistance			25°C		1000		GΩ	
C <sub>IC</sub>	Common-mode input capacitance	f = 100 Hz		25°C		5		pF	

<sup>†</sup> Full range is 0°C to 70°C for C suffix and –40°C to 125°C for I suffix. If not specified, full range is –40°C to 125°C.



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# electrical characteristics at specified free-air temperature, $V_{DD}$ = 3 V and 5 V (unless otherwise noted) (continued)

#### output characteristics

	PARAMETER	TEST CONDITI	ONS	T <sub>A</sub> †	MIN	TYP	MAX	UNITS	
			Jan - 10 mA	25°C	2.7	2.97			
		\\\2\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	I <sub>OH</sub> = -10 mA	Full range	2.7			\	
	High-level output voltage	$V_{DD} = 3 \text{ V},  V_{IC} = V_{DD}/2$	I <sub>OH</sub> =–100 mA	25°C	2.6	2.73			
			10H = 100 III/K	Full range	2.6				
			I <sub>OH</sub> = -10 mA	25°C	4.7	4.96			
Vон			IOH = -10 IIIA	Full range	4.7				
		$V_{DD} = 5 \text{ V},  V_{IC} = V_{DD}/2$	100 mA	25°C	4.6	4.76			
			I <sub>OH</sub> = -100 mA	Full range	4.6			] v	
			I <sub>OH</sub> = -200 mA	25°C	4.45	4.6			
				−40°C to 85°C	4.35				
			I <sub>OL</sub> = 10 mA	25°C		0.03	0.1	- - - V	
		V <sub>DD</sub> = 3 V and 5 V,	IOL = 10 IIIA	Full range			0.1		
		$V_{IC} = V_{DD}/2$	100 mA	25°C		0.33	0.4		
VOL	Low-level output voltage		I <sub>OL</sub> = 100 mA	Full range			0.55		
				25°C		0.38	0.6		
		$V_{DD} = 5 \text{ V},  V_{IC} = V_{DD}/2$	I <sub>OL</sub> = 200 mA	−40°C to 85°C			0.7		
10	Output current <sup>‡</sup> Measured at 0.5 V from rail	Maggurad at 0.5 V from roil	V <sub>DD</sub> = 3 V	25°C		±220		mA	
Ю		weasured at 0.5 v nom fall	V <sub>DD</sub> = 5 V	25°C		±320		mA	
loo	Sourcing		25°C			800	·	mΛ	
los	Short-circuit output current‡	Sinking		23 0		800		mA	

<sup>†</sup> Full range is 0°C to 70°C for C suffix and -40°C to 125°C for I suffix. If not specified, full range is -40°C to 125°C.

#### power supply

	PARAMETER	TEST CONDITIONS	TA	MIN	TYP	MAX	UNITS
1	Cupply gurrent (pay shappel)	V- V/2	25°C		700	1000	
IDD	Supply current (per channel) $V_O = V_{DD}/2$	Full range			1500	μΑ	
		V <sub>DD</sub> =2.7 to 3.3 V, No load,	25°C	70	82		
DCDD	Downer cumply rejection ratio (AV) = (AV) =	$V_{IC} = V_{DD}/2 V$	Full range	65			dB
PSRR	Power supply rejection ratio (ΔV <sub>DD</sub> / ΔV <sub>IO</sub> )	V <sub>DD</sub> =4.5 to 5.5 V, No load,	25°C	70	79		uБ
		$V_{IC} = V_{DD}/2 V$	Full range	65			

<sup>†</sup> Full range is 0°C to 70°C for C suffix and -40°C to 125°C for I suffix. If not specified, full range is -40°C to 125°C.



<sup>‡</sup>When driving output currents in excess of 200 mA, the MSOP PowerPAD package is required for thermal dissipation.

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# electrical characteristics at specified free-air temperature, $V_{DD}$ = 3 V and 5 V (unless otherwise noted) (continued)

#### dynamic performance

	PARAMETER	TEST CONDITIONS	S	T <sub>A</sub> †	MIN	TYP	MAX	UNITS	
GBWP	Gain bandwidth product	R <sub>L</sub> =100 Ω	C <sub>L</sub> =10 pF	25°C		2.7		MHz	
	Slew rate at unity gain		V <sub>DD</sub> = 3 V	25°C	0.8	1.57		<i>M</i> -	
SR		$R_L = 100 \Omega$ ,	vDD = 2 v	Full range	0.55				
SK			V <sub>DD</sub> = 5 V	25°C	1	1.57		V/μs	
				Full range	0.7				
φМ	Phase margin	D 400.0	D. 100 O. C.	C: - 10 pE	25°C		66		
	Gain margin	$R_L = 100 \Omega$ ,	C <sub>L</sub> = 10 pF	25°C		16		dB	
	Settling time	V(STEP)pp = 1 V, AV = -1,	0.1%	25°C		0.7			
l t <sub>S</sub>		$C_L = 10 \text{ pF},$ $R_L = 100 \Omega$		250		1.3		μs	

<sup>†</sup> Full range is 0°C to 70°C for C suffix and -40°C to 125°C for I suffix. If not specified, full range is -40°C to 125°C.

### noise/distortion performance

PARAMETER TEST CONDITION		TEST CONDITIONS		T <sub>A</sub>	MIN	TYP	MAX	UNITS
THD+N	Total harmonic distortion plus noise	VO(nn) = VDD/2 V	A <sub>V</sub> = 1		0.025 0.035			
		$V_{O(pp)} = V_{DD}/2 V$ , $R_{L} = 100 \Omega$ ,	A <sub>V</sub> = 10	25°C				
		f = 100 Hz	A <sub>V</sub> = 100		(	0.15		
V	Familiar time of paris and the second	f = 100 Hz		25 C		55		->///
V <sub>n</sub>	Equivalent input noise voltage	f = 10 kHz				10		nV/√Hz
In	Equivalent input noise current	f = 1 kHz			(	0.31		fA/√Hz

#### shutdown characteristics

	PARAMETER	TEST CONDITIONS	T <sub>A</sub> †	MIN	TYP	MAX	UNITS	
lan (0.17.1)	Supply current in shutdown mode (per channel)	SHDN = 0 V	25°C		3.4	10		
IDD(SHDN)	(TLV4110, TLV4113)	SHUN = 0 V	Full range			15	μΑ	
t(ON)	Amplifier turnon time‡	D. 400.0	25°C		1			
t(Off)	Amplifier turnoff time‡	R <sub>L</sub> = 100 Ω	25 0		3.3		μs	

Full range is 0°C to 70°C for C suffix and -40°C to 125°C for I suffix. If not specified, full range is -40°C to 125°C.



Disable time and enable time are defined as the interval between application of the logic signal to SHDN and the point at which the supply current has reached half its final value.

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#### **TYPICAL CHARACTERISTICS**

## **Table of Graphs**

			FIGURE
V <sub>IO</sub>	Input offset voltage	vs Common-mode input voltage	1, 2
CMRR	Common-mode rejection ratio	vs Frequency	3
Vон	High-level output voltage	vs High-level output current	4, 6
VOL	Low-level output voltage	vs Low-level output current	5, 7
Z <sub>o</sub>	Output impedance	vs Frequency	8
I <sub>DD</sub>	Supply current	vs Supply voltage	9
ksvr	Power supply voltage rejection ratio	vs Frequency	10
AVD	Differential voltage amplification and phase	vs Frequency	11
	Gain-bandwidth product	vs Supply voltage	12
SR	Slew rate	vs Supply voltage	13
	Siew rate	vs Temperature	14
	Total harmonic distortion+noise	vs Frequency	15
Vn	Equivalent input voltage noise	vs Frequency	16
	Phase margin	vs Capacitive load	17
	Voltage-follower signal pulse response		18, 19
	Inverting large-signal pulse response		20, 21
	Small-signal inverting pulse response		22
	Crosstalk	vs Frequency	23
	Shutdown forward and reverse isolation		24
	Shutdown supply current	vs Free-air temperature	25
	Shutdown supply current/output voltage		26



#### TYPICAL CHARACTERISTICS

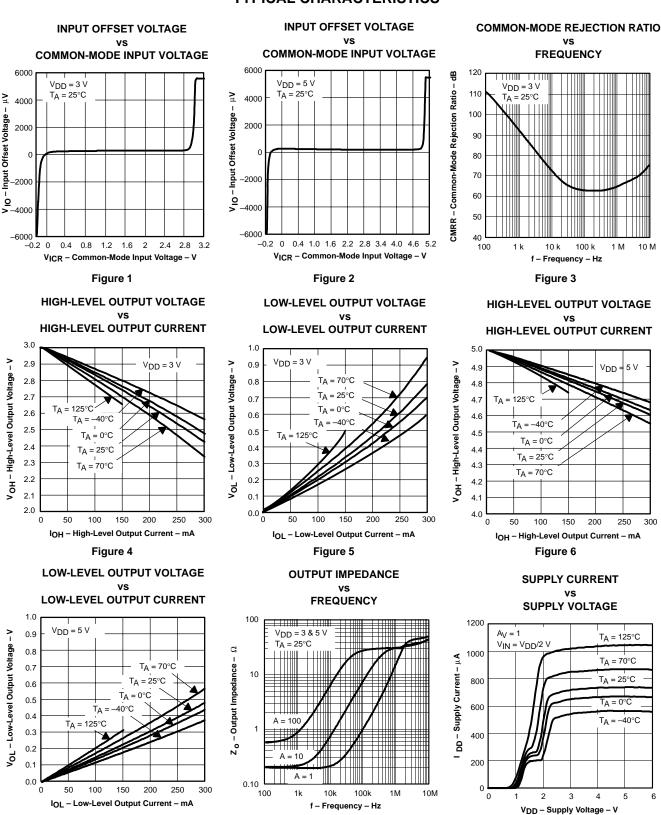




Figure 8

Figure 9

Figure 7

**DIFFERENTIAL VOLTAGE** 

#### TYPICAL CHARACTERISTICS

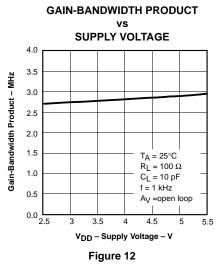
#### **POWER SUPPLY REJECTION RATIO FREQUENCY** 100 V<sub>DD</sub> = 3 & 5 V PSRR - Power Supply Rejection Ratio - V 90 $R_F = 1 k\Omega$ R<sub>I</sub> = 100 Ω 80 $V_{IN} = 0 V$ 70 T<sub>A</sub> = 25°C 60 50 40 30 20 10 0 100 f - Frequency - Hz

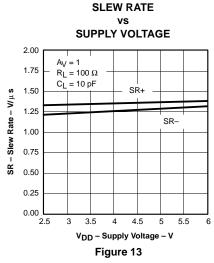
**AMPLIFICATION AND PHASE** vs **FREQUENCY** 쁑 120 135 A VD - Differential Voltage Amplification 100 PHASE 80 90 Phase Margin 60 40 GAIN 20 V<sub>DD</sub> = 3 & 5 V 0  $R_L = 100 \text{ k}\Omega$  $C_L = 10 pF$ -20 $T_A = 25^{\circ}C$ -40 100 100 k 10 M

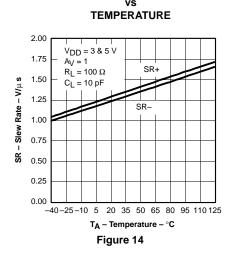
Figure 10

Figure 11

f - Frequency - Hz





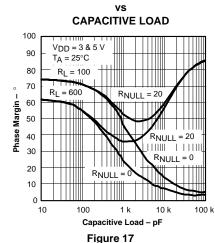


**SLEW RATE** 

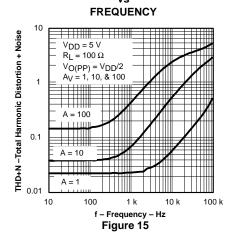
TOTAL HARMONIC DISTORTION+NOISE

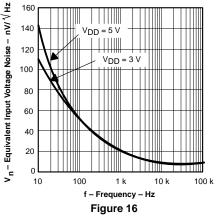
EQUIVALENT INPUT VOLTAGE NOISE
vs
FREQUENCY

160
VDD = 5 V

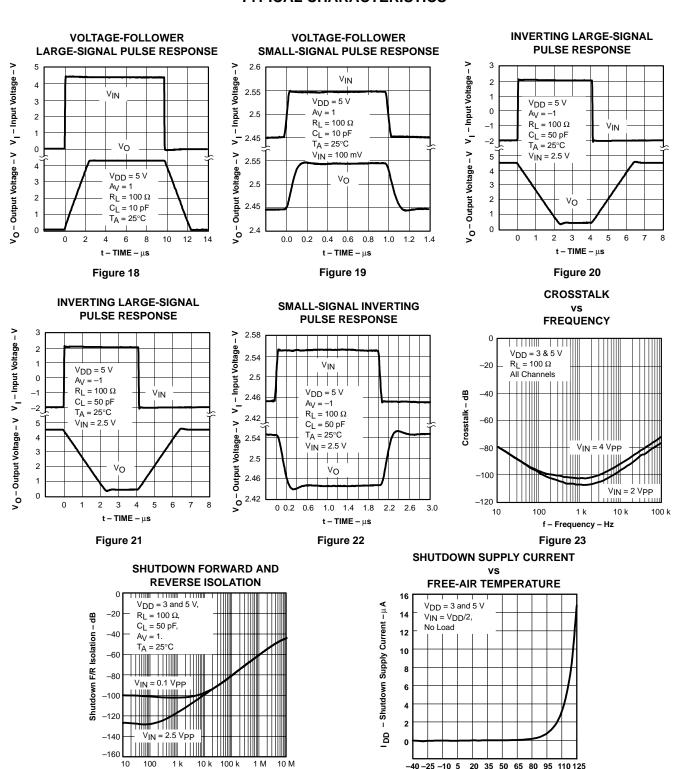


**PHASE MARGIN** 





#### TYPICAL CHARACTERISTICS





TA - Free-Air Temperature - °C

Figure 25

f - Frequency - Hz

Figure 24

#### **TYPICAL CHARACTERISTICS**

#### SHUTDOWN SUPPLY CURRENT / OUTPUT VOLTAGE

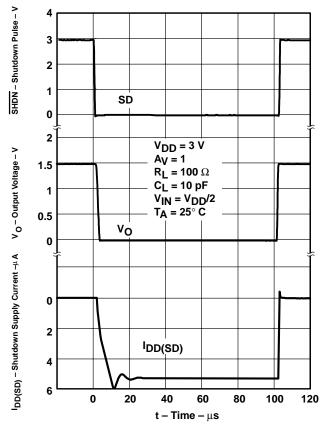


Figure 26

#### **APPLICATION INFORMATION**

#### shutdown function

Two members of the TLV411x family (TLV4110/3) have a shutdown terminal for conserving battery life in portable applications. When the shutdown terminal is tied low, the supply current is reduced to just nano amps per channel, the amplifier is disabled, and the outputs are placed in a high impedance mode. In order to save power in shutdown mode, an external pullup resistor is required, therefore, to enable the amplifier the shutdown terminal must be pulled high. When the shutdown terminal is left floating, care should be taken to ensure that parasitic leakage current at the shutdown terminal does not inadvertently place the operational amplifier into shutdown.

#### driving a capacitive load

When the amplifier is configured in this manner, capacitive loading directly on the output will decrease the device's phase margin leading to high frequency ringing or oscillations. Therefore, for capacitive loads of greater than 1 nF, it is recommended that a resistor be placed in series ( $R_{NULL}$ ) with the output of the amplifier, as shown in Figure 27. A maximum value of 20  $\Omega$  should work well for most applications.

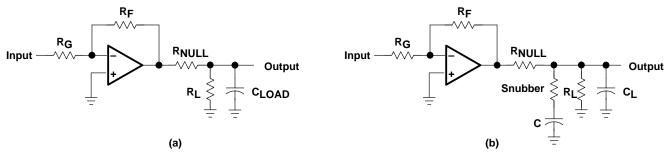


Figure 27. Driving a Capacitive Load

### offset voltage

The output offset voltage,  $(V_{OO})$  is the sum of the input offset voltage  $(V_{IO})$  and both input bias currents  $(I_{IB})$  times the corresponding gains. The following schematic and formula can be used to calculate the output offset voltage:

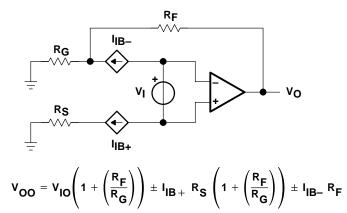


Figure 28. Output Offset Voltage Model



#### APPLICATION INFORMATION

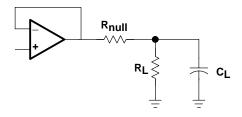


Figure 29

#### general power design considerations

When driving heavy loads at high junction temperatures there is an increased probability of electromigration affecting the long term reliability of ICs. Therefore for this not to be an issue either:

• The output current must be limited (at these high junction temperatures).

or

• The junction temperature must be limited.

The maximum continuous output current at a die temperature 150°C will be 1/3 of the current at 105°C.

The junction temperature will be dependent on the ambient temperature around the IC, thermal impedance from the die to the ambient and power dissipated within the IC.

$$T_J = T_A + \theta_{JA} \times P_{DIS}$$

#### Where:

P<sub>DIS</sub> is the IC power dissipation and is equal to the output current multiplied by the voltage dropped across the output of the IC.

 $\theta_{\text{JA}}$  is the thermal impedance between the junction and the ambient temperature of the IC.

T<sub>J</sub> is the junction temperature.

 $T_A$  is the ambient temperature.

Reducing one or more of these factors results in a reduced die temperature. The 8-pin SOIC (small outline integrated circuit) has a thermal impedance from junction to ambient of 176°C/W. For this reason it is recommended that the maximum power dissipation of the 8-pin SOIC package be limited to 350 mW, with peak dissipation of 700 mW as long as the RMS value is less than 350 mW.

The use of the MSOP PowerPAD™ dramatically reduces the thermal impedance from junction to case. And with correct mounting, the reduced thermal impedance greatly increases the IC's permissible power dissipation and output current handling capability. For example, the power dissipation of the PowerPAD™ is increased to above 1 W. Sinusoidal and pulse-width modulated output signals also increase the output current capability. The equivalent dc current is proportional to the square-root of the duty cycle:

$$I_{DC(EQ)} = I_{Cont} \times \sqrt{\text{(duty cycle)}}$$

CURRENT DUTY CYCLE AT PEAK RATED CURRENT	EQUIVALENT DC CURRENT AS A PERCENTAGE OF PEAK
100	100
70	84
50	71

Note that with an operational amplifier, a duty cycle of 70% would often result in the op amp sourcing current 70% of the time and sinking current 30%, therefore, the equivalent dc current would still be 0.84 times the continuous current rating at a particular junction temperature.



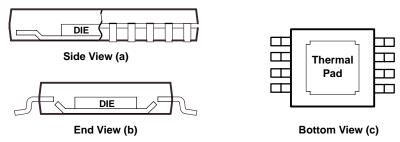
#### APPLICATION INFORMATION

#### general PowerPAD design considerations

The TLV411x is available in a thermally-enhanced PowerPAD family of packages. These packages are constructed using a downset leadframe upon which the die is mounted [see Figure 30(a) and Figure 30(b)]. This arrangement results in the lead frame being exposed as a thermal pad on the underside of the package [see Figure 30(c)]. Because this thermal pad has direct thermal contact with the die, excellent thermal performance can be achieved by providing a good thermal path away from the thermal pad.

The PowerPAD package allows for both assembly and thermal management in one manufacturing operation. During the surface-mount solder operation (when the leads are being soldered), the thermal pad can also be soldered to a copper area underneath the package. Through the use of thermal paths within this copper area, heat can be conducted away from the package into either a ground plane or other heat dissipating device.

The PowerPAD package represents a breakthrough in combining the small area and ease of assembly of surface mount with the, heretofore, awkward mechanical methods of heatsinking.



NOTE A: The thermal pad is electrically isolated from all terminals in the package.

Figure 30. Views of Thermally Enhanced DGN Package

Although there are many ways to properly heatsink the PowerPAD package, the following steps illustrate the recommended approach.

#### Thermal Pad Area

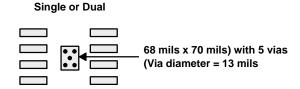


Figure 31. PowerPAD PCB Etch and Via Pattern



#### APPLICATION INFORMATION

#### general PowerPAD design considerations (continued)

- 1. Prepare the PCB with a top side etch pattern as shown in Figure 31. There should be etch for the leads as well as etch for the thermal pad.
- 2. Place five holes (dual) or nine holes (quad) in the area of the thermal pad. These holes should be 13 mils in diameter. Keep them small so that solder wicking through the holes is not a problem during reflow.
- 3. Additional vias may be placed anywhere along the thermal plane outside of the thermal pad area. This helps dissipate the heat generated by the TLV411x IC. These additional vias may be larger than the 13-mil diameter vias directly under the thermal pad. They can be larger because they are not in the thermal pad area to be soldered so that wicking is not a problem.
- 4. Connect all holes to the internal ground plane.
- 5. When connecting these holes to the ground plane, do not use the typical web or spoke via connection methodology. Web connections have a high thermal resistance connection that is useful for slowing the heat transfer during soldering operations. This makes the soldering of vias that have plane connections easier. In this application, however, low thermal resistance is desired for the most efficient heat transfer. Therefore, the holes under the TLV411x PowerPAD package should make their connection to the internal ground plane with a complete connection around the entire circumference of the plated-through hole.
- 6. The top-side solder mask should leave the terminals of the package and the thermal pad area with its five holes (dual) or nine holes (quad) exposed. The bottom-side solder mask should cover the five or nine holes of the thermal pad area. This prevents solder from being pulled away from the thermal pad area during the reflow process.
- 7. Apply solder paste to the exposed thermal pad area and all of the IC terminals.
- 8. With these preparatory steps in place, the TLV411x IC is simply placed in position and run through the solder reflow operation as any standard surface-mount component. This results in a part that is properly installed.

For a given  $\theta_{JA}$ , the maximum power dissipation is shown in Figure 32 and is calculated by the following formula:

$$P_D = \left(\frac{T_{MAX} - T_A}{\theta_{JA}}\right)$$

Where:

P<sub>D</sub> = Maximum power dissipation of TLV411x IC (watts)

 $T_{MAX}$  = Absolute maximum junction temperature (150°C)

 $T_A$  = Free-ambient air temperature (°C)

 $\theta_{JA} = \theta_{JC} + \theta_{CA}$ 

 $\theta_{JC}$  = Thermal coefficient from junction to case

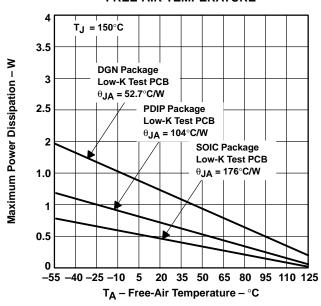
 $\theta_{CA}$  = Thermal coefficient from case to ambient air (°C/W)



#### **APPLICATION INFORMATION**

#### general PowerPAD design considerations (continued)

## MAXIMUM POWER DISSIPATION vs FREE-AIR TEMPERATURE



NOTE A: Results are with no air flow and using JEDEC Standard Low-K test PCB.

Figure 32. Maximum Power Dissipation vs Free-Air Temperature

The next consideration is the package constraints. The two sources of heat within an amplifier are quiescent power and output power. The designer should never forget about the quiescent heat generated within the device, especially multi-amplifier devices. Because these devices have linear output stages (Class A-B), most of the heat dissipation is at low output voltages with high output currents.

The other key factor when dealing with power dissipation is how the devices are mounted on the PCB. The PowerPAD devices are extremely useful for heat dissipation. But, the device should always be soldered to a copper plane to fully use the heat dissipation properties of the PowerPAD. The SOIC package, on the other hand, is highly dependent on how it is mounted on the PCB. As more trace and copper area is placed around the device,  $\theta_{JA}$  decreases and the heat dissipation capability increases. The currents and voltages shown in these graphs are for the total package. For the dual or quad amplifier packages, the sum of the RMS output currents and voltages should be used to choose the proper package.



#### APPLICATION INFORMATION

#### macromodel information

Macromodel information provided was derived using Microsim  $Parts^{TM}$ , the model generation software used with Microsim  $PSpice^{TM}$ . The Boyle macromodel (see Note 3) and subcircuit in Figure 33 are generated using the TLV411x typical electrical and operating characteristics at  $T_A = 25^{\circ}C$ . Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases):

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- Input bias current
- Open-loop voltage amplification

- Unity-gain frequency
- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit

NOTE 3: G. R. Boyle, B. M. Cohn, D. O. Pederson, and J. E. Solomon, "Macromodeling of Integrated Circuit Operational Amplifiers," *IEEE Journal of Solid-State Circuits*, SC-9, 353 (1974).

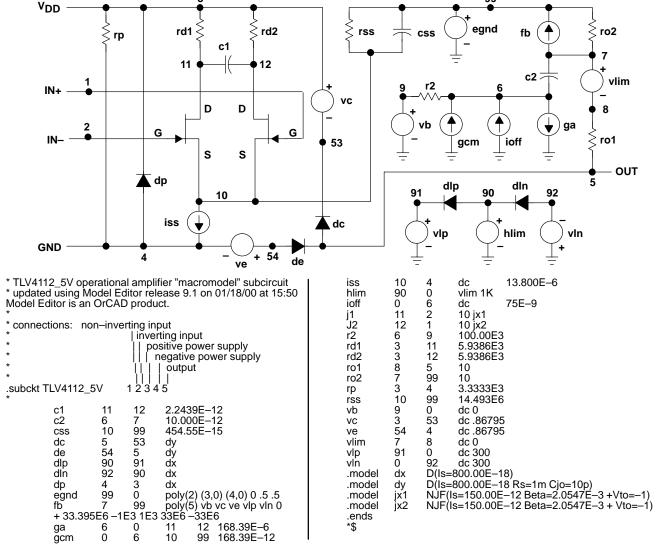


Figure 33. Boyle Macromodel and Subcircuit

PSpice and Parts are trademarks of MicroSim Corporation.



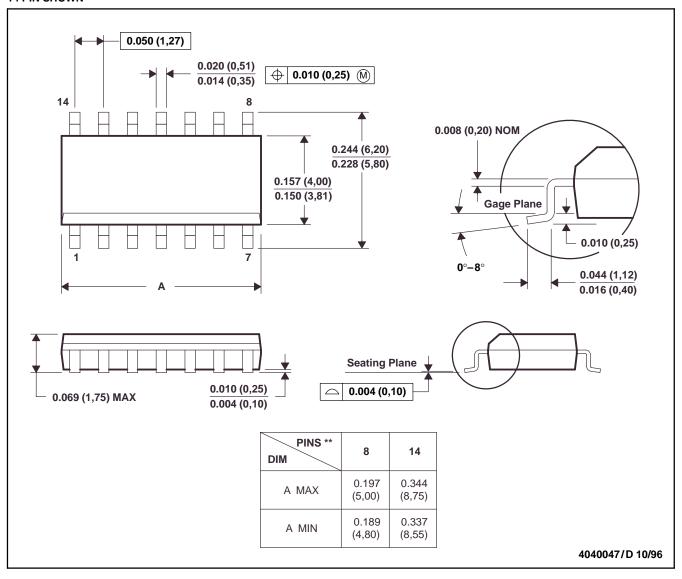
SLOS289D - DECEMBER 1999 - REVISED FEBRUARY 2002

#### **MECHANICAL DATA**

#### D (R-PDSO-G\*\*)

#### 14 PIN SHOWN

#### PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0.006 (0,15).

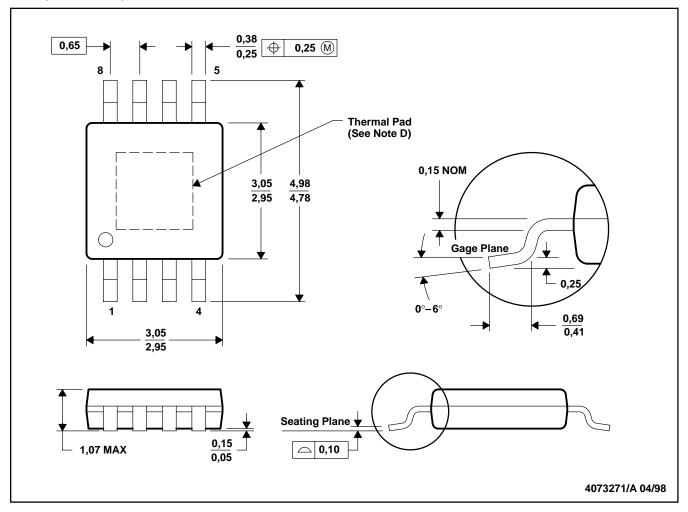
D. Falls within JEDEC MS-012



#### **MECHANICAL INFORMATION**

#### DGN (S-PDSO-G8)

#### PowerPAD™ PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions include mold flash or protrusions.
- D. The package thermal performance may be enhanced by attaching an external heat sink to the thermal pad. This pad is electrically and thermally connected to the backside of the die and possibly selected leads.
- E. Falls within JEDEC MO-187

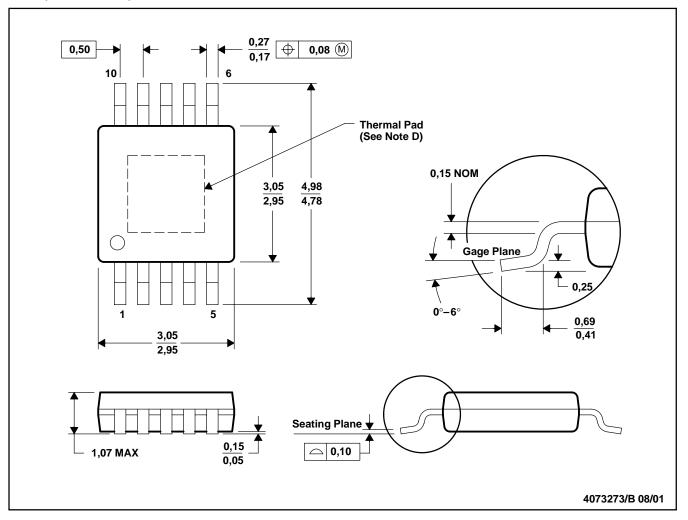
PowerPAD is a trademark of Texas Instruments.



#### **MECHANICAL INFORMATION**

#### DGQ (S-PDSO-G10)

#### PowerPAD™ PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. The package thermal performance may be enhanced by bonding the thermal pad to an external thermal plane. This pad is electrically and thermally connected to the backside of the die and possibly selected leads.
- E. Falls within JEDEC MO-187

PowerPAD is a trademark of Texas Instruments.

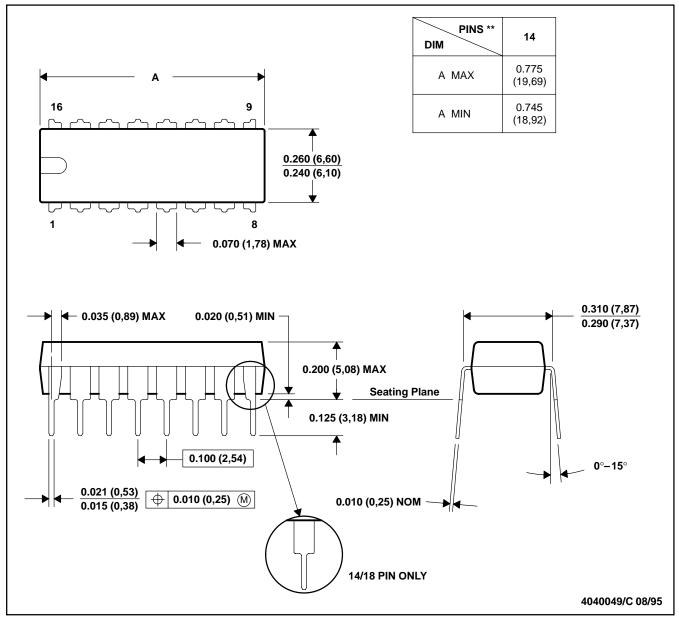


#### **MECHANICAL INFORMATION**

#### N (R-PDIP-T\*\*)

#### **16 PIN SHOWN**

#### PLASTIC DUAL-IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

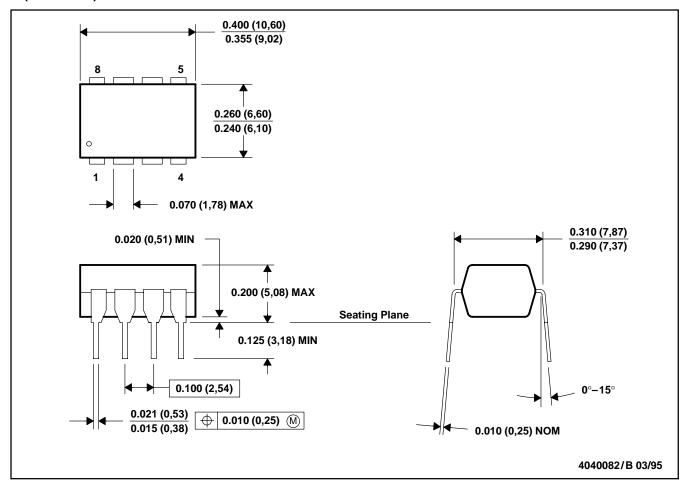
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 (20 pin package is shorter then MS-001.)



#### **MECHANICAL INFORMATION**

#### P (R-PDIP-T8)

#### PLASTIC DUAL-IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Falls within JEDEC MS-001



### **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
TLV4110CD	ACTIVE	SOIC	D	8	75	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
TLV4110CDGN	ACTIVE	MSOP- Power PAD	DGN	8	80	None	CU NIPDAU	Level-1-220C-UNLIM
TLV4110CDGNR	ACTIVE	MSOP- Power PAD	DGN	8	2500	None	CU NIPDAU	Level-1-220C-UNLIM
TLV4110CDR	ACTIVE	SOIC	D	8	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
TLV4110CP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	Level-NC-NC-NC
TLV4110ID	ACTIVE	SOIC	D	8	75	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
TLV4110IDGN	ACTIVE	MSOP- Power PAD	DGN	8	80	None	CU NIPDAU	Level-1-220C-UNLIM
TLV4110IDGNR	ACTIVE	MSOP- Power PAD	DGN	8	2500	None	CU NIPDAU	Level-1-220C-UNLIM
TLV4110IDR	ACTIVE	SOIC	D	8	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
TLV4110IP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	Level-NC-NC-NC
TLV4111CD	ACTIVE	SOIC	D	8	75	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
TLV4111CDGN	ACTIVE	MSOP- Power PAD	DGN	8	80	None	CU NIPDAU	Level-1-220C-UNLIM
TLV4111CDGNR	ACTIVE	MSOP- Power PAD	DGN	8	2500	None	CU NIPDAU	Level-1-220C-UNLIM
TLV4111CDR	ACTIVE	SOIC	D	8	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
TLV4111CP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	Level-NC-NC-NC
TLV4111ID	ACTIVE	SOIC	D	8	75	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
TLV4111IDGN	ACTIVE	MSOP- Power PAD	DGN	8	80	None	CU NIPDAU	Level-1-220C-UNLIM
TLV4111IDGNR	ACTIVE	MSOP- Power PAD	DGN	8	2500	None	CU NIPDAU	Level-1-220C-UNLIM
TLV4111IDR	ACTIVE	SOIC	D	8	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
TLV4111IP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	Level-NC-NC-NC
TLV4112CD	ACTIVE	SOIC	D	8	75	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
TLV4112CDGN	ACTIVE	MSOP-	DGN	8	80	None	CU NIPDAU	Level-1-220C-UNLIM





22-Feb-2005

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
		Power PAD						
TLV4112CDGNR	ACTIVE	MSOP- Power PAD	DGN	8	2500	None	CU NIPDAU	Level-1-220C-UNLIM
TLV4112CDR	ACTIVE	SOIC	D	8	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR Level-1-220C-UNLIM
TLV4112CP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	Level-NC-NC-NC
TLV4112ID	ACTIVE	SOIC	D	8	75	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR Level-1-220C-UNLIM
TLV4112IDGN	ACTIVE	MSOP- Power PAD	DGN	8	80	None	CU NIPDAU	Level-1-220C-UNLIM
TLV4112IDGNR	ACTIVE	MSOP- Power PAD	DGN	8	2500	None	CU NIPDAU	Level-1-220C-UNLIM
TLV4112IDR	ACTIVE	SOIC	D	8	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR Level-1-220C-UNLIM
TLV4112IP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	Level-NC-NC-NC
TLV4113CD	ACTIVE	SOIC	D	14	50	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR Level-1-220C-UNLIM
TLV4113CDGQ	ACTIVE	MSOP- Power PAD	DGQ	10	80	None	CU SNPB	Level-1-220C-UNLIM
TLV4113CDGQR	ACTIVE	MSOP- Power PAD	DGQ	10	2500	None	CU SNPB	Level-1-220C-UNLIM
TLV4113CDR	ACTIVE	SOIC	D	14	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR Level-1-220C-UNLIM
TLV4113CN	ACTIVE	PDIP	N	14	25	None	Call TI	Call TI
TLV4113ID	ACTIVE	SOIC	D	14	50	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR Level-1-220C-UNLIM
TLV4113IDGQ	ACTIVE	MSOP- Power PAD	DGQ	10	80	None	CU SNPB	Level-1-220C-UNLIM
TLV4113IDGQR	ACTIVE	MSOP- Power PAD	DGQ	10	2500	None	CU SNPB	Level-1-220C-UNLIM
TLV4113IDR	ACTIVE	SOIC	D	14	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAF Level-1-220C-UNLIM
TLV4113IN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPD	Level-NC-NC-NC

 $<sup>^{(1)}</sup>$  The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> Eco Plan - May not be currently available - please check http://www.ti.com/productcontent for the latest availability information and additional



#### PACKAGE OPTION ADDENDUM

22-Feb-2005

product content details.

None: Not yet available Lead (Pb-Free).

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Green (RoHS & no Sb/Br): TI defines "Green" to mean "Pb-Free" and in addition, uses package materials that do not contain halogens, including bromine (Br) or antimony (Sb) above 0.1% of total product weight.

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDECindustry standard classifications, and peak solder temperature.

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